

ABSTRACT OF THE DISCLOSURE

The present invention relates to a plating method and a plating apparatus which can attain embedding of copper into fine interconnection patterns with use of a plating liquid having high throwing power and leveling properties, and which can make 5 film thickness of a plated film substantially equal between an interconnection region and a non-interconnection region. A plating method comprises filling a plating liquid containing metal ions and an additive into a plating space formed between a substrate and an anode disposed closely to the substrate so as to face the substrate, and changing concentration of the additive in the plating liquid filled into the plating space during a plating process.

10